PTO/SB/08A (05-03)
Approved for use through 05/31/2003. OMB 0651-0031
U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE
o a collection of information unless it displays a wild OMF.

Substitute for form 1449A/PTO						Complete if Known					
Capatitate to total property						Application Number TBD					
INFORMATION DISCLOSURE STATEMENT BY APPLICANT						<del></del>		<del>                                     </del>	lerewith		
								<del>                                     </del>			
								<del></del>	Yeo, et al.		
(uso as many shoats as nacessary)						Art Unit TBD					
(use as many sheets as necessary)					Examiner Name TBD						
Sheet	Sheet 1 of			1		Attorney Docket Number		TSM03-0511			
U.S. PATENT DOCUMENTS											
Cumplant	Cito	Document Num	Publication Date MM-DD-YYYY		Name of Patentee or Applicant of Cited Document			Pages, Columns, Lines, Where		e	
Examiner Initials*	Cite No.	Number - Kind Code <sup>2 (# known)</sup>					Relevant Passages or Relevant Figures Appear		u		
5	Α	US-6,252,284 B1		06-26-2001		Muller, et al.					
8	В	US-6,391,695 B1		05-21-2002		Yu					
<u>X</u>	C	US-6,391,782 B1		05-21,2002		Yu					
8	D	US-6,413,802 B1		07-02-2002		Hu, et al.					
4	E	US-6,432,829 B1		08-13-2002 09-17-2002		Muller, et al.		<del>-4</del>			
0	G	US-6,451,656 B1 US-6,492,212 B1		12-10-2002		Yu, et al					
3	1	US-		12-10-2002		l seong, c		- 1			
FOREIGN PATENT DOCUMENTS											
	Γ	Foreign Pa	atent Docum						Pages, Columns, Lin	nes,	1
Examiner	Cite		Publ		tion Date Name of Patente D-YYYY Applicant of Cited Do			Where Relevant Passages		TS	
Initials* No. 1 Country Code3 - Number4 - Kind Code5 (ii			e <sup>5</sup> (if known)					or Relevant Figures Appear			
	-										
		<u> </u>					<u></u>		<u> </u>		
OTHER PRIOR ART NON PATENT LITERATURE DOCUMENTS											
			OTHER I	PRIOR ART	NON PA	TENT LI	TERATURE DOCU	MENTS			
	1	tnc					TERATURE DOCUI		of the	,	
Examiner	Cite	tro	lude name of	the author (in CAP	ITAL LETTI serial, symp	RS), title of osium, catal	the article (when appropri og, etc.), date, page(s), vo	ate), title (		τ2	
Examiner Initials*	No.		lude name of item (book, r	the author (in CAP magazine, journal, s number(s), put	ITAL LETTI serial, symp olisher, city	RS), title of osium, catal and/or coun	the article (when appropri og, etc.), date, page(s), vo try where published.	iate), title d olume-issu	8	٦²	
	Cite <sub>1</sub> No.		lude name of item (book, r	the author (in CAP magazine, journal, s number(s), put	ITAL LETTI serial, symp olisher, city	RS), title of osium, catal and/or coun	the article (when appropri og, etc.), date, page(s), vo try where published.	iate), title d olume-issu	8	τ²	
	No.	HUANG, X., e Devices, Vol. 4	tude name of item (book, r t al. "Sub 18, No. 5	the author (in CAP) magazine, journal, s number(s), put 0-50 nm P-Ch (May 2001)	serial, sympolisher, city nannel F pp. 880	ers), title of osium, catal and/or countries, "-886.	the article (when appropri og, etc.), date, page(s), vo try where published.  'IEEE Transaction	iate), title ( okume-issu ons on l	Electron	τ²	
	H.	HUANG, X., e Devices, Vol. 4	tude name of item (book, r t al. "Sub 18, No. 5	the author (in CAP) magazine, journal, s number(s), put 0-50 nm P-Ch (May 2001)	serial, sympolisher, city nannel F pp. 880	ers), title of osium, catal and/or countries, "-886.	the article (when appropri og, etc.), date, page(s), vo try where published.  'IEEE Transaction	iate), title ( okume-issu ons on l	Electron	۲²	
	No.	HUANG, X., e Devices, Vol. 4	tude name of item (book, r t al. "Sub 18, No. 5	the author (in CAP) magazine, journal, s number(s), put 0-50 nm P-Ch (May 2001)	serial, sympolisher, city nannel F pp. 880	ers), title of osium, catal and/or countries, "-886.	the article (when appropri og, etc.), date, page(s), vo try where published.	iate), title ( okume-issu ons on l	Electron	τ²	
	H I	HUANG, X., e Devices, Vol. 4 YANG, F.L., e of Technical Pa	item (book, r t al. "Sub 18, No. 5 t al. "35r apers, (Ju	the author (in CAP) magazine, journal, s number(s), put p-50 nm P-Ch (May 2001) nm CMOS Fi nne 2002) pp.	serial, sympolisher, city nannel Fpp. 880	ers), title of osium, catal and/or countinFET," -886.	the article (when appropriog, etc.), date, page(s), vo try where published.  IEEE Transaction  Symposium on VI.	ons on l	e Electron chnology Digest	τ²	
	H.	HUANG, X., e Devices, Vol. 4 YANG, F.L., e of Technical Pa	item (book, r t al. "Sub 18, No. 5 t al. "35r apers, (Ju	the author (in CAP) magazine, journal, s number(s), put p-50 nm P-Ch (May 2001) nm CMOS Fi nne 2002) pp.	serial, sympolisher, city nannel Fpp. 880	ers), title of osium, catal and/or countinFET," -886.	the article (when appropriog, etc.), date, page(s), vo try where published.  IEEE Transaction  Symposium on VI.	ons on l	e Electron chnology Digest	τ²	
	H I	HUANG, X., e Devices, Vol. 4 YANG, F.L., e of Technical Pa	item (book, r t al. "Sub 18, No. 5 t al. "35r apers, (Ju	the author (in CAP) magazine, journal, s number(s), put p-50 nm P-Ch (May 2001) nm CMOS Fi nne 2002) pp.	serial, sympolisher, city nannel Fpp. 880	ers), title of osium, catal and/or countinFET," -886.	the article (when appropri og, etc.), date, page(s), vo try where published.  'IEEE Transaction	ons on l	e Electron chnology Digest	72	
	No.'	HUANG, X., e Devices, Vol. 4 YANG, F.L., e of Technical Pa WONG, HS.I Development (	t al. "Sub t al. "Sub t al. "Sub t al. "35r t al. "35r apers, (Ju P. "Beyor March/M	the author (in CAP) magazine, journal, s number(s), put p-50 nm P-Ch (May 2001) nm CMOS Fi ine 2002) pp. nd the Conve	ital Letti serial, symp polisher, city nannel F pp. 880 nFETs, 109-11 ntional	ers), title of osium, catal and/or countinFET,"-886. " 2002 S 0. Transist	the article (when appropriog, etc.), date, page(s), votry where published.  IEEE Transaction  Symposium on VI.  or," IBM Journal	of Res	electron chnology Digest	72	
	H I	HUANG, X., e Devices, Vol. 4 YANG, F.L., e of Technical Pa WONG, HS.I Development (	t al. "Sub t al. "Sub t al. "Sub t al. "35r t al. "35r apers, (Ju P. "Beyor March/M	the author (in CAP) magazine, journal, s number(s), put p-50 nm P-Ch (May 2001) nm CMOS Fi ine 2002) pp. nd the Conve	ital Letti serial, symp polisher, city nannel F pp. 880 nFETs, 109-11 ntional	ers), title of osium, catal and/or countinFET,"-886. " 2002 S 0. Transist	the article (when appropriog, etc.), date, page(s), votry where published.  IEEE Transaction  Symposium on VI.  or," IBM Journal	of Res	electron chnology Digest	,2	
	No.'	HUANG, X., e Devices, Vol. 4  YANG, F.L., e of Technical Pa  WONG, HS.I Development (  CHAU, R., e16 Tri-gate," Exte and Materials,	t al. "Subtestance of item (book, r t al. "Subtestance of t al. "35rapers, (Ju P. "Beyon March/M	the author (in CAP) magazine, journal, s number(s), put p-50 nm P-Ch (May 2001) nm CMOS Fi nne 2002) pp. nd the Conve lay 2002) pp. nced Deplete stracts of the p. 68-69.	orial territorial sympolisher, city nannel Fpp. 880 nFETs, 109-11 ntional, 133-16 ed-Subs 2002 Ir	RS), title of osium, catal and/or coun in FET, "-886." 2002 S 0.  Transistor. Transistor. Transistor.	the article (when appropriog, etc.), date, page(s), votry where published.  THEE Transaction  Tymposium on VI.  Tymposium on VI.	of Res	Electron  chnology Digest  earch and  ouble-gate and State Devices	,2	
	No.'	HUANG, X., e Devices, Vol. 4  YANG, F.L., e of Technical Pa  WONG, HS.I Development (  CHAU, R., e16 Tri-gate," Exte and Materials,	t al. "Subtestance of item (book, r t al. "Subtestance of t al. "35rapers, (Ju P. "Beyon March/M	the author (in CAP) magazine, journal, s number(s), put p-50 nm P-Ch (May 2001) nm CMOS Fi nne 2002) pp. nd the Conve lay 2002) pp. nced Deplete stracts of the p. 68-69.	orial territorial sympolisher, city nannel Fpp. 880 nFETs, 109-11 ntional, 133-16 ed-Subs 2002 Ir	RS), title of osium, catal and/or coun in FET, "-886." 2002 S 0.  Transistor. Transistor. Transistor.	the article (when appropriog, etc.), date, page(s), votry where published.  THEE Transaction  Tymposium on VI.  Tymposium on VI.	of Res	Electron  chnology Digest  earch and  ouble-gate and State Devices	,2	
	No. H	HUANG, X., e Devices, Vol. 4  YANG, F.L., e of Technical Pa  WONG, HS.I Development (  CHAU, R., e16 Tri-gate," Exte and Materials,	t al. "Subtestance of item (book, r t al. "Subtestance of t al. "35rapers, (Ju P. "Beyon March/M	the author (in CAP) magazine, journal, s number(s), put p-50 nm P-Ch (May 2001) nm CMOS Fi nne 2002) pp. nd the Conve lay 2002) pp. nced Deplete stracts of the p. 68-69.	orial territorial sympolisher, city nannel Fpp. 880 nFETs, 109-11 ntional, 133-16 ed-Subs 2002 Ir	RS), title of osium, catal and/or coun in FET, "-886." 2002 S 0.  Transistor. Transistor. Transistor.	the article (when appropriog, etc.), date, page(s), votry where published.  IEEE Transaction  Symposium on VI.  or," IBM Journal	of Res	Electron  chnology Digest  earch and  ouble-gate and State Devices	,2	
	H I	HUANG, X., e Devices, Vol. 4  YANG, F.L., e of Technical Pa  WONG, HS.I Development (  CHAU, R., et a Tri-gate," Exte and Materials, YANG, F.L., e Digest of Tech	tude name of item (book, r tal. "Sub 18, No. 5 tal. "35r apers, (Ju 2. "Beyon March/March Advanded Ab (2002) pt al. "25r nical Pap	the author (in CAP) magazine, journal, s number(s), put p-50 nm P-Ch (May 2001) nm CMOS Fi ine 2002) pp. nd the Conve fay 2002) pp. nced Deplete stracts of the p. 68-69. hm CMOS Opers, (December)	orial terrial sympolisher, city nannel F pp. 880 nFETs, 109-11 ntional 133-16 ed-Subs 2002 Ir mega F ber 200	RS), title of osium, catal and/or coun in FET, "-886. " 2002 S 0. Transistiff. trate Transternatio ETS," In 2) pp. 25	the article (when appropriog, etc.), date, page(s), votry where published.  IEEE Transaction  Symposium on VI.  or," IBM Journal  ansistors: Single-gual Conference of ternational Electricity-258.	on SI Tecorda Solida So	Electron Chnology Digest earch and Duble-gate and State Devices	72	
	No. H	HUANG, X., e Devices, Vol. 4  YANG, F.L., e of Technical Pa  WONG, HS.I Development (  CHAU, R., et a Tri-gate," Exte and Materials, YANG, F.L., e Digest of Tech	tal. "Subtal. "Subtal. "Subtal. "Subtal. "Subtal. "35rapers, (Jul. "Beyon March/Mul. "Advanded Ab. (2002) pt al. "25rnical Papers."	the author (in CAP) magazine, journal, s number(s), put p-50 nm P-Ch (May 2001) nm CMOS Fi nne 2002) pp. and the Conve lay 2002) pp. nnced Deplete stracts of the p. 68-69. mm CMOS O pers, (Decemb	mal Letting serial, sympolisher, city nannel F pp. 880 nFETs, 109-11 ntional 133-16 ed-Subs 2002 Ir mega F ber 200 stulator	ers), title of osium, catal and/or coun in FET, "-886. " 2002 S O. Transisti7. trate Tratternatio ETs," In 2) pp. 25	the article (when appropriog, etc.), date, page(s), votry where published.  THEE Transaction  Tymposium on VI.  Tymposium on VI.	on SI Tecorda Solida So	Electron Chnology Digest earch and Duble-gate and State Devices	72	
	H I K	HUANG, X., e Devices, Vol. 4  YANG, F.L., e of Technical Pa  WONG, HS.I Development (  CHAU, R., et a Tri-gate," Exte and Materials,  YANG, F.L., e Digest of Tech  COLINGE, J.P. Electron Device	t al. "Subta la	the author (in CAP) magazine, journal, s number(s), put p-50 nm P-Ch (May 2001)  mm CMOS Fi ane 2002) pp. and the Conve lay 2002) pp. and the Conve lay 2002) pp. and the Conve lay 2002) pp. and CMOS Opers, (Decemilary), (1990) pp. and the Convers, (Decemilary), (1990) pp.	nral Letting serial, sympolisher, city nannel F pp. 880 nFETs, 109-11 ntional, 133-16 ed-Subs 2002 in mega F ber 200 nsulator co. 595-5	RS), title of osium, catal and/or coun in FET, "-886. " 2002 S 0. Transist 17. trate Traternatio ETs," In 2) pp. 25	the article (when appropriog, etc.), date, page(s), votry where published.  IEEE Transaction  Symposium on VI.  or," IBM Journal  unsistors: Single-gual Conference of ternational Electricity 25-258.  All-Around Device.	of Resonate, Don Dever," In	electron chnology Digest earch and ouble-gate and State Devices vices Meeting, ternational	72	
	H I	HUANG, X., e Devices, Vol. 4  YANG, F.L., e of Technical Pr  WONG, HS.I Development (  CHAU, R., et a Tri-gate, "Exte and Materials, YANG, F.L., e Digest of Tech  COLINGE, J.P Electron Device	tude name of item (book, r tal. "Subtem (book, r tal. "Subtem (book, r tal. "35r tapers, (Jule 2002) p. "Beyon March/March (2002) p. tal. "25r nical Papers (g., et al." es Meeti	the author (in CAP) magazine, journal, s number(s), put p-50 nm P-Ch (May 2001) nm CMOS Fi the 2002) pp. and the Conve flay 2002) pp. mced Deplete fistracts of the p. 68-69. nm CMOS Opers, (Decembers, (Decembers) Silicon-on-Iring, (1990) pp. Vire-Channel	orial sympolisher, city namnel F pp. 880 nFETs, 109-11 ntional 133-16 ed-Subs 2002 ir mega F ber 200 nsulator o. 595-5 and wr	ers), title of osium, catal and/or countinfer, "-886." 2002 S 0.  Transist of trate Transist of trate Transist of the Transis of t	the article (when appropriog, etc.), date, page(s), vo try where published.  IEEE Transaction  Symposium on VI.  Or," IBM Journal  Linsistors: Single-gual Conference of ternational Electricity-258.  All-Around Deviced.	of Res  cate, Do  de-sem	Electron  Chnology Digest  earch and  Duble-gate and State Devices  vices Meeting,  ternational	72	
	H I K	HUANG, X., e Devices, Vol. 4  YANG, F.L., e of Technical Pa  WONG, HS.I Development (  CHAU, R., et a Trigate, "Exte and Materials, YANG, F.L., e Digest of Tech  COLINGE, J.P Electron Device  LEOBANDUM effect transisto	tal. "Subtales item (book, range) tal. "Subtales, No. 5 tal. "35rapers, (Jud. "Beyon March/March	the author (in CAP) magazine, journal, s number(s), put p-50 nm P-Ch (May 2001) nm CMOS Fi ine 2002) pp. and the Conve lay 2002) pp. nced Deplete stracts of the p. 68-69. nm CMOS O pers, (Decemil Silicon-on-Ir ng, (1990) pp. Vire-Channel significant re	nral Letriserial, sympolisher, city nannel F pp. 880 nrFETs, 109-11 ntional 133-16 ed-Subs 2002 Ir mega F ber 200 nsulator 5. 595-5 and wreduction	ers), title of osium, catal and/or coun in FET, "-886." 2002 S 0.  Transist i7.  trate Trate Traternatio  ETs," In 2) pp. 25 "Gate -198.  ap-aroun of short	the article (when appropriog, etc.), date, page(s), votry where published.  IEEE Transaction  Symposium on VI.  Or," IBM Journal  Insistors: Single-gnal Conference of ternational Electricity (15-258.  All-Around Device the channel effects.	of Res  ate, Do  ate, Do  cate, Do  cate, Do  de-sem  ' Journ	electron chnology Digest earch and cuble-gate and State Devices vices Meeting, ternational	72	
	H I K	HUANG, X., e Devices, Vol. 4  YANG, F.L., e of Technical Pa  WONG, HS.I Development (  CHAU, R., et a Trigate, "Exte and Materials, YANG, F.L., e Digest of Tech  COLINGE, J.P Electron Device  LEOBANDUM effect transisto	tal. "Subtales item (book, range) tal. "Subtales, No. 5 tal. "35rapers, (Jud. "Beyon March/March	the author (in CAP) magazine, journal, s number(s), put p-50 nm P-Ch (May 2001) nm CMOS Fi ine 2002) pp. and the Conve lay 2002) pp. nced Deplete stracts of the p. 68-69. nm CMOS O pers, (Decemil Silicon-on-Ir ng, (1990) pp. Vire-Channel significant re	nral Letriserial, sympolisher, city nannel F pp. 880 nrFETs, 109-11 ntional 133-16 ed-Subs 2002 Ir mega F ber 200 nsulator 5. 595-5 and wreduction	ers), title of osium, catal and/or coun in FET, "-886." 2002 S 0.  Transist i7.  trate Trate Traternatio  ETs," In 2) pp. 25 "Gate -198.  ap-aroun of short	the article (when appropriog, etc.), date, page(s), vo try where published.  IEEE Transaction  Symposium on VI.  Or," IBM Journal  Linsistors: Single-gual Conference of ternational Electricity-258.  All-Around Deviced.	of Res  ate, Do  ate, Do  cate, Do  cate, Do  de-sem  ' Journ	electron chnology Digest earch and cuble-gate and State Devices vices Meeting, ternational	-2	
	H I I K K I K	HUANG, X., e Devices, Vol. 4  YANG, F.L., e of Technical Pa  WONG, HS.I Development (  CHAU, R., et a Trigate, "Exte and Materials, YANG, F.L., e Digest of Tech  COLINGE, J.P Electron Device  LEOBANDUM effect transisto	tal. "Subtales item (book, range) tal. "Subtales, No. 5 tal. "35rapers, (Jud. "Beyon March/March	the author (in CAP) magazine, journal, s number(s), put p-50 nm P-Ch (May 2001) nm CMOS Fi ine 2002) pp. and the Conve lay 2002) pp. nced Deplete stracts of the p. 68-69. nm CMOS O pers, (Decemil Silicon-on-Ir ng, (1990) pp. Vire-Channel significant re	nral Letriserial, sympolisher, city nannel F pp. 880 nrFETs, 109-11 ntional 133-16 ed-Subs 2002 Ir mega F ber 200 nsulator 5. 595-5 and wreduction	ers), title of osium, catal and/or coun in FET, "-886." 2002 S 0.  Transist i7.  trate Trate Traternatio  ETs," In 2) pp. 25 "Gate -198.  ap-aroun of short	the article (when appropriog, etc.), date, page(s), votry where published.  IEEE Transaction  Symposium on VI.  Or," IBM Journal  Insistors: Single-gnal Conference of ternational Electricity (15-258.  All-Around Device the channel effects.	of Resonate, Don Dever," Inde-sem, 'Journ 17) pp.	electron chnology Digest earch and cuble-gate and State Devices vices Meeting, ternational iconductor field- al of Vacuum 2791-2794.	12	

"EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. Applicant's unique citation designation number (optional). See Kinds Codes of USPTO Patent Documents at <a href="https://www.uspto.gov">www.uspto.gov</a> or MPEP 901.04. Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. Side of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. Applicant

This collection of information is required by 37 CFR 1.97 and 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 2 hours to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this turden, should be sent to the Chief Information Officer, U.S. Petent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450.